NSN 5961-01-338-2170

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-338-2170 **Inclosure Material:** Metal **Overall Length:** 1.252 inches **Overall Height:** Between 0.250 inches and 0.340 inches Overall Width: 0.700 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 collector to emitter voltage/static/base open and 80.0 collector to base voltage, dc and 5.0 emitter to base voltage, dc **Current Rating Per Characteristic:** 8.00 amperes source cutoff current and 120.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 75.0 watts small-signal input power, common-collector absolute **Transfer Ratio:** 4.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

No

NSN 5961-01-338-2170 Transistor - Page 2 of 2



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